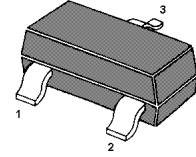


Plastic-Encapsulate Transistors

TRANSISTOR (NPN)

for microwave low noise amplifier at VHF, UHF and CATV band

The transistor is subdivided into three groups, Q, R and S, according to its DC current gain.



SOT-23-3L Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	20	V
Collector Emitter Voltage	V_{CEO}	12	V
Emitter Base Voltage	V_{EBO}	3	V
Collector Current	I_C	100	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_S	- 65 to + 150	$^\circ\text{C}$

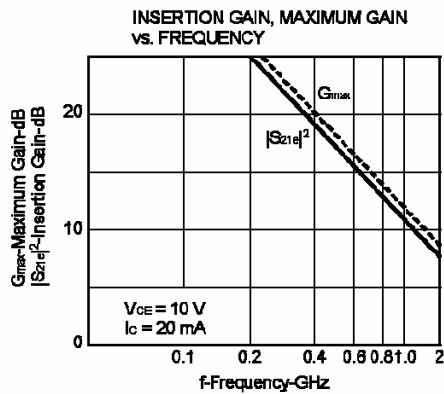
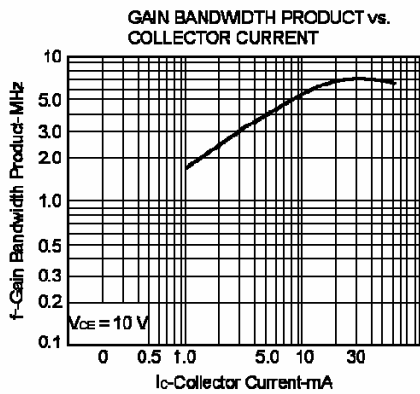
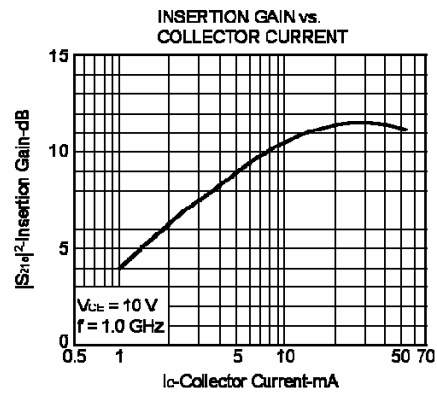
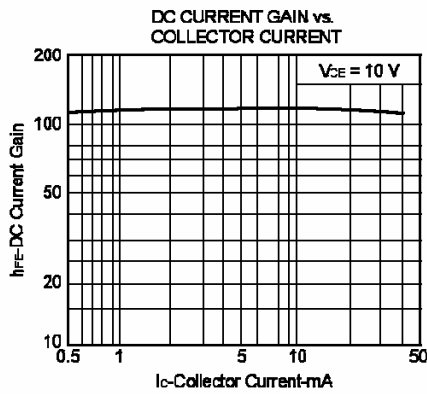
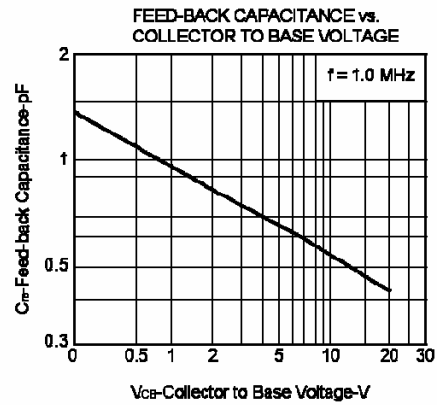
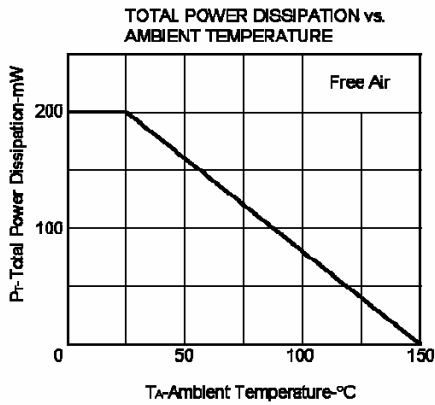
Characteristics ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 10\text{ V}$, $I_C = 20\text{ mA}$ Current Gain Group	Q	50	-	100	-
	R	80	-	160	-
	S	125	-	250	-
	h_{FE}				
Collector Cutoff Current at $V_{CB} = 10\text{ V}$	I_{CBO}	-	-	1	μA
Emitter Cutoff Current at $V_{EB} = 1\text{ V}$	I_{EBO}	-	-	1	μA
Gain Bandwidth Product at $V_{CE} = 10\text{ V}$, $I_C = 20\text{ mA}$	f_T	-	7	-	GHz
Feed-Back Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	$C_{re}^{1)}$	-	0.55	1	pF
Noise Figure at $V_{CE} = 10\text{ V}$, $I_C = 7\text{ mA}$, $f = 1\text{ GHz}$	NF	-	1.1	2	dB

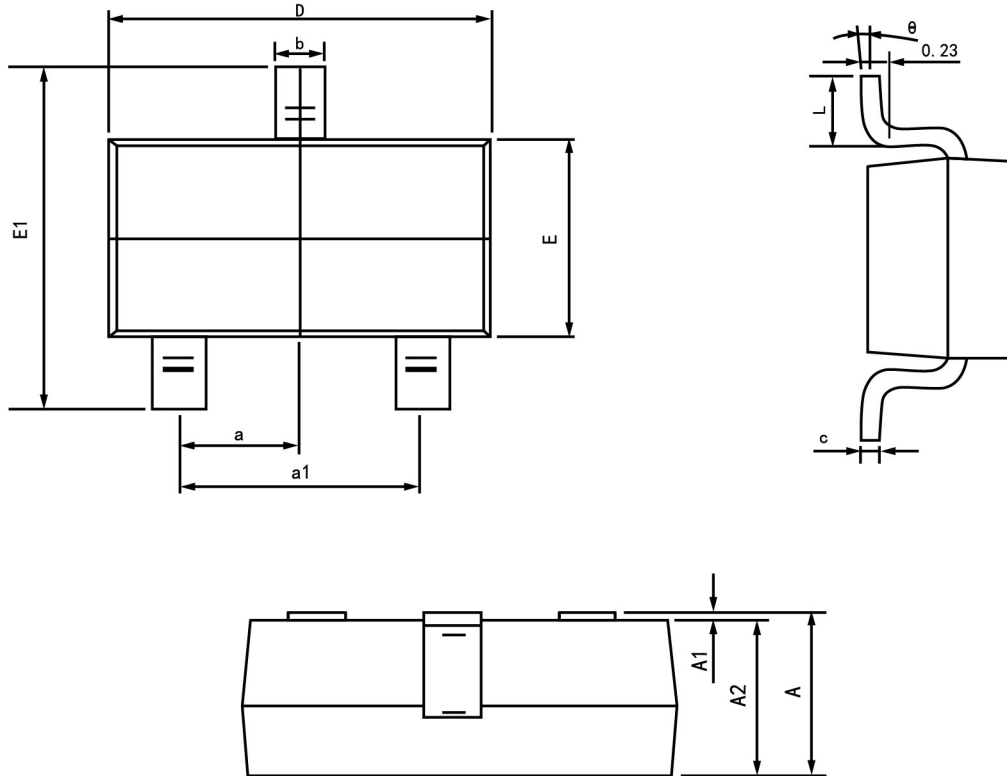
¹⁾ The emitter terminal and the case shall be connected to the guard terminal of the three-terminal capacitance bridge.

CLASSIFICATION OF $h_{FE(1)}$

Rank	Q	R	S
Range	50-100	80-160	125-250
MARKING	R23	R24	R25



SOT-23-3L Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.820	3.020
E	1.500	1.700
E1	2.650	2.950
e	0.950 (Basic)	
e1	1.800	2.000
L	0.300	0.600
θ	0°	8°